



FORM PTO-1449 (Rev. 7-80) Trademark Office	U.S. Dept. of Commerce Patent and	Atty. Docket No. 422.04	Appl. No. 10/052,049
LIST OF REFERENCES CITED BY APPLICANT		Applicant: CHEN, Ling, et al.	
(Use several sheets if necessary)		Filing Date: Jan 16, 2002	

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1	4,058,430	15-Nov-1977	Method For Producing Compound Thin Films			25-Nov-1975
	4,389,973	28-Jun-1983	Apparatus For Performing Growth of Compound Thin Films			11-Dec-1981
	4,413,022	1-Nov-1983	Method For Performing Growth of Compound Thin Films			21-Jun-1979
	4,767,494	30-Aug-1988	Preparation process of compound semiconductor			19-Sep-1986
	4,806,321	21-Feb-1989	Use of infrared radiation and an ellipsoidal reflection mirror			25-Jul-1985
	4,840,921	20-Jun-1989	Process for the growth of III-V group compound semiconductor crystal on a Si substrate			30-Jun-1988
	4,845,049	4-Jul-1989	Doping III-V compound semiconductor devices with group VI monolayers using ALE			28-Mar-1988
	4,859,627	22-Aug-1989	Group VI doping of III-V semiconductors during ALE			1-Jul-1988
	4,861,417	29-Aug-1989	Method of growing group III-V compound semiconductor epitaxial layer			24-Mar-1988
	4,876,218	24-Oct-1989	Method of growing GaAs films on Si or GaAs substrates using ALE			26-Sep-1988
	4,993,357	19-Feb-1991	Apparatus for atomic layer epitaxial growth			21-Dec-1989
	5,082,798	21-Jan-1992	Crystal growth method			27-Sep-1990
	5,130,269	14-Jul-1992	Hetero-epitaxially grown compound semiconductor substrate and a method of growing the same			25-Apr-1989
	5,166,092	24-Nov-1992	Method of growing compound semiconductor epitaxial layer by atomic layer epitaxy			30-Oct-1990
	5,225,366	6-Jul-1993	Apparatus For and a Method of Growing Thin Films Elemental Semiconductors			22-Jun-1990
	5,250,148	5-Oct-1993	Process for growing GaAs monocrystal film			12-Nov-1991
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THM	5,316,793	31-May-1994	Directed Effusive Beam Atomic Layer Epitaxy System and Method			27-Jul-1992

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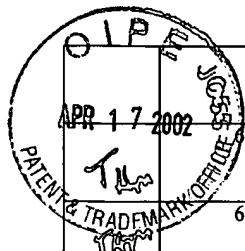
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	6,043,177	28-Mar-2000	Modification of zeolite or molecular sieve membranes using atomic layer controlled chemical vapor deposition			21-Jan-1997
	6,090,442	18-Jun-2000	Method of growing films on substrates at room temperatures using catalyzed binary reaction sequence chemistry			2-Oct-1997
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	6,174,377	16-Jan-2001	Processing Chamber for Atomic Layer Deposition Processes			4-Jan-1999
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	6,291,876	18-Sep-2001	Electronic devices with composite atomic barrier film and process for making same			20-Aug-1998
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	6,306,216	23-Oct-2001	Apparatus for deposition of thin films on wafers through atomic layer epitaxial process			12-Jul-2000
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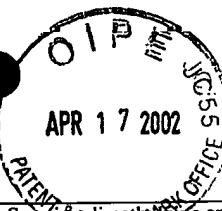
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